

2SD2621

Silicon NPN epitaxial planar type

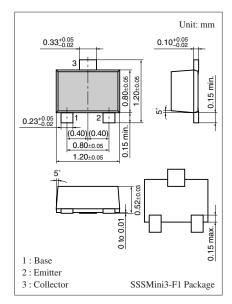
For low-frequency driver amplification

■ Features

- High forward current transfer ratio hFE
- Low collector-emitter saturation voltage V_{CE(sat)}
- ullet High emitter-base voltage (Collector open) V_{EBO}

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	100	V	
Collector-emitter voltage (Base open)	V _{CEO}	100	V	
Emitter-base voltage (Collector open)	V_{EBO}	15	V	
Collector current	I_C	20	mA	
Peak collector current	I_{CP}	50	mA	
Collector power dissipation	P _C	100	mW	
Junction temperature	T_{j}	125	°C	
Storage temperature	T _{stg}	-55 to +125	°C	



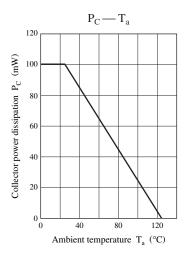
Marking Symbol: 3B

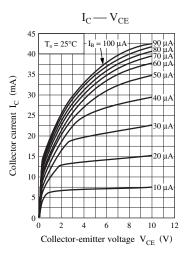
\blacksquare Electrical Characteristics $~T_a = 25^{\circ}C \pm 3^{\circ}C$

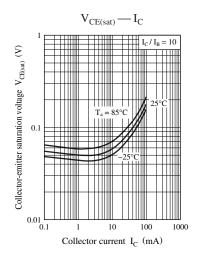
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = 10 \ \mu A, I_E = 0$	100			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	100			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \ \mu A, \ I_C = 0$	15			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 60 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 60 \text{ V}, I_{B} = 0$			1.0	μΑ
Forward current transfer ratio	h_{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	400		1 200	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$		0.05	0.20	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Noise voltage	NV	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}, G_{V} = 80 \text{ dB}$		80		mV
		$R_g = 100 \text{ k}\Omega$, Function = FLAT				

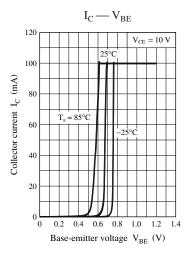
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

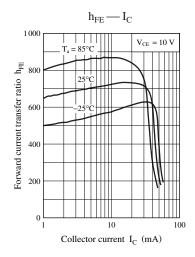
Panasonic

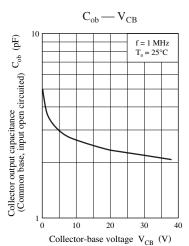












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